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Enthalpy of formation for Cu-Zn-Sn-S (CZTS)

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Herein we report an analytical procedure to calculate the enthalpy of formation for thin film multinary compounds from sputtering rates measured during ion bombardment. The method is based on Sigmund's sputtering theory and the Born-Haber cycle. Using this procedure, an enthalpy of formation for a CZTS film of the composition $Cu_{1.9}Zn_{1.5}Sn_{0.8}S_4$ was measured as –930±98 kJ/mol. This value is much more negative than the sum of the enthalpies of formation for the constituent binary compounds, meaning the multinary formation reaction is predicted to be exothermic. (Supporting information is available at http://arxiv.org/abs/1403.4496)

Cu_2ZnSnS_4 (CZTS) has generated tremendous interest as an earth abundant, low-cost alternative to Cu(In,Ga)Se_2 (CIGS), which is one of the key photoabsorber materials in commercial thin film solar cells. As is often the case, the potentially low-cost alternative presents challenges in terms of performance. For CZTS, great emphasis was initially placed on getting the best device performance, and power conversion efficiencies have rapidly saturated at 9–11%.[1,2] The direction is now to improve the material to reach the 20% power conversion efficiency mark.[2] It is believed that to reach that high performance level, CZTS must be better understood at a fundamental level. One fundamental parameter that remains experimentally unknown is the standard enthalpy of formation. There have been two values reported that were calculated using density function theory (DFT); –337 kJ/mol reported by Maeda et al.[3] and –406 kJ/mol reported by Walsh et al.[4] However, to our knowledge, no experimental measurements have been made. The small sample mass of thin films makes measurement of thermochemical properties using traditional techniques challenging. Thus there is a need for alternative techniques that can measure small amount of sample.

Herein we report an approach to calculate the standard enthalpy of formation from measured relative sputtering rates under ion bombardment in the low energy regime (surface binding energy $\ll$ projectile energy $<$ 1 keV). The method relies upon the use of an internal standard that has known composition and enthalpy of formation. Using Sigmund's formula for sputtering yield in the low energy regime, the ratio of the sputtering rate of the internal standard to the sputtering rate of the unknown material, both measured at the same current density and ion energy, are used together with the measured composition of the unknown material to calculate the surface binding energy (U_0) of atoms in the unknown. The Born-Haber cycle is then used to convert the surface binding energy to the enthalpy of formation, given the measured composition of the unknown sample.

We believe that the method can be applied using data from common surface science tools such as x-ray photoelectron and Auger electron spectrometers (XPS and AES) and different types of secondary ion mass spectrometers (SIMS) if the instrument is equipped with an ion mill so composition profiles can be measured. Such measurements should be within the capabilities of many laboratories around the world, and we hope to see the thermochemical tables start to fill with data on other interesting multinary compounds.

The composition profiles of three different samples were used for this study. All three samples were prepared by atomic layer deposition (ALD) and the composition profiles were measured by time of flight (TOF) SIMS. Experimental details can be found in previous reports.[5,6] The samples were 92 nm CZTS ($Cu_{1.9}Zn_{1.5}Sn_{0.8}S_4$) coated by either 20 nm of ALD ZnO, 22 nm of ALD ZnS or nothing.

The three SIMS depth profiles, which were used to measure relative sputtering rates, are presented in Fig.1. Each profile was measured at the same Ar^+ current density and projectile energy (E_p=250 eV). The experimentally-measured sputtering rate was calculated by dividing the layer thickness by the time it took to sputter through it:

$$SR_{exp} = \frac{d}{t}, \quad (1)$$

where d is the known layer thickness and t is the time it took to sputter through it during the measurement of the composition profile.

The sputtering rate, which has units of length per time, can be written as:

$$SR_{theory} = \frac{J \cdot Y}{e \cdot n}, \quad (2)$$

where J is the ion current density, Y is the sputtering yield (i.e. the number of ejected atoms per incident ion), e is the elementary charge and n is the atomic density of the target material with units of atoms per volume. The atomic density can be calculated if the composition and mass density are known by:

$$n = \frac{\rho}{M_t}, \quad (3)$$

where ρ is the mass density of the target material and M_t is the number average atomic mass in the target material. M_t can be calculated by:

$$M_t = \frac{\sum \nu_i \cdot M_i}{\sum \nu_i}, \quad (4)$$

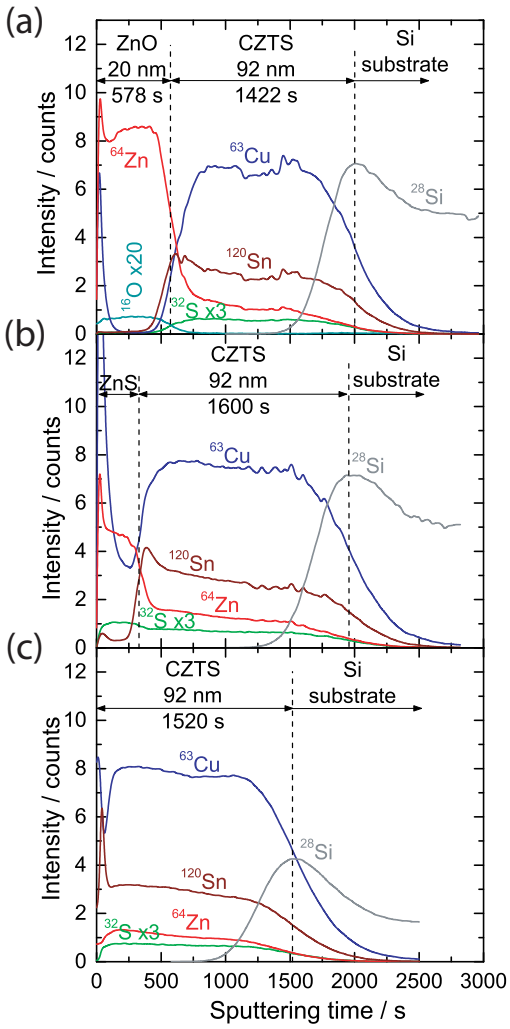

FIG. 1: **TOF SIMS composition profiles of 92 nm ALD CZTS films coated with (a) 20 nm ALD ZnO; (b) 22 nm ALD ZnS; and (c) uncoated.**

where ν_i is the number of atoms of element i in the target molecule and M_i is the atomic mass of element i. The sputtering yield can be calculated in the near-threshold (low) energy regime using Sigmund's formula:[7]

$$Y = \frac{3}{4\pi^2} \cdot \frac{\alpha \cdot \gamma}{U_0} \cdot E_p, \quad (5)$$

where α and γ are functions of M_t and the projectile atomic mass, E_p is the projectile energy and U_0 is the surface binding energy of atoms in the target material, which has units of energy per atom. The surface binding energy U_0 is the link to the thermodynamic properties of the target material and that will be discussed later. The following formula can be used to calculate γ:[7]

$$\gamma = \frac{4 \cdot M_t \cdot M_p}{(M_t + M_p)^2}, \quad (6)$$

where M_p is the atomic mass of the projectile, Ar^+ in this case, and M_t can be calculated using Eq.(4). Different authors have reported different functions for the parameter α, and they agree to within 10% of the value. We chose to use the popular expression of Matsunami et al.:[8]

$$\alpha = 0.08 + 0.164 \cdot \left(\frac{M_t}{M_p}\right)^{0.4} + 0.0145 \cdot \left(\frac{M_t}{M_p}\right)^{1.29}. \quad (7)$$

For two different materials bombarded by ions at the same conditions, the ratio of the sputtering rate of material 2 to the sputtering rate of material 1 can be predicted as a function of the surface binding energy, atomic density and average atomic mass by:

$$\left(\frac{SR_2}{SR_1}\right)_{theory} = \frac{U_{0,1}}{U_{0,2}} \cdot \frac{n_1}{n_2} \cdot \frac{\alpha_2}{\alpha_1} \cdot \frac{\gamma_2}{\gamma_1}. \quad (8)$$

If the composition and densities are known, then the only unknowns on the right-hand-side in Eq.(8) are the surface binding energies $U_{0,1}$ and $U_{0,2}$.

It is important to mention that it has been observed experimentally that greater than 99.4% of the gas-phase species produced by Ar^+ bombardment of GaAs in the low energy regime are neutral Ga and As atoms.[9] Thus, sputtering of a material, such as the inorganic sulfides and oxides considered here, by Ar^+ in the low energy regime may be approximated as an ideal process of generating gaseous atoms from the solid. The energy penalty associated with promoting the atoms from the solid into the gas phase is the surface binding energy, U_0.

The Born-Haber cycle is a theoretical thermodynamic cycle that involves two different paths to transform atoms from their condensed state in a solid into a liberated gas-phase state (Fig.S5). One path involves first transforming the compound into its constituent elements at their standard state, which requires an energy change equal to the negative of the enthalpy of formation. The second step is the generation of gaseous atoms from the elements in their standard state, which involves vaporizing condensed phases and breaking any bonds that may be present in molecular elements (e.g. elemental sulfur or oxygen). The other path from the solid to gaseous atoms treats the solid as a collection of ions. The first step is to liberate the ions into the gas phase from the crystal lattice, which involves an energy penalty equal to the lattice energy. The second step is to generate neutral gas-phase atoms from gas-phase ions, which involves an energy change equal to the negative of the sum of the ionization energies for the atoms in the compound. Putting the preceding discussion into mathematical form, we may write:

$$\begin{aligned} E_{coh} &= U_0 \cdot \sum \nu_i = \\ &= -\Delta H_f^0 + \Big(\sum \nu_i \cdot \Delta H_{vap,i} + \\ &+ \sum_{anions} \nu_i \cdot \eta_i \cdot D^0_{molecule,i} \Big) = E_{lattice} - E_{ion}, \quad (9) \end{aligned}$$

where E_{coh} is the cohesive energy of the molecule, which is simply the surface binding energy of an atom in that

material multiplied by the number of atoms in a molecule, ΔH_f^0 is the enthalpy of formation, $\Delta H_{vap,i}$ is the enthalpy of vaporization for element i, η_i is the number of bonds per atom in elemental molecules (i.e. η=1 for sulfur), $D^0_{molecule,i}$ is the energy required to break a bond in an elemental molecule (e.g. O_2 or S_8) in order to generate free atoms, and E_{ion} is the energy required to generate the ions with the same formal charge as that in the material (e.g. Cu^+, Zn^{2+}, Sn^{4+}, S^{2-}, O^{2-}, Mg^{2+} and etc.). E_{ion} can be calculated using the following equation:

$$E_{ion} = \sum_{cations} \left(\nu_{M_i} \cdot \sum_{j=1}^{n} I(M_i^{j+}) \right) + \\ + \sum_{anions} \left(\nu_{A_i} \cdot \sum_{j=1}^{m} I(A_i^{j-}) \right), \quad (10)$$

where ν_{M_i} is the number of atoms of cation i in a molecule, $I(M_i^{j+})$ is the ionization energy of the process $M_i^{(j-1)+} \rightarrow M_i^{j+}$, n is the formal charge of cation i in the material, ν_{A_i} is the number of atoms of anion i in a molecule, $I(A_i^{j-})$ is the electron affinity of the process $A_i^{(j-1)-} \rightarrow A_i^{j-}$ and m is the formal charge of anion i in the material. An example calculation can be found in the supporting information. Eq.(9) is the key connection between the surface binding energy in the sputtering process and tabulated thermodynamic data.

To verify that the model predictions agree reasonably well with the experimentally-measured sputtering rates, Eqs.(8) and (9) were used to predict the relative sputtering rates of materials with known thermodynamic properties. This was performed by comparing the sputtering rate of ZnO to MgO and also by comparing ZnS to ZnO (see supporting information). The predicted sputtering rate of ZnO is 2.1 times higher than MgO; while the experimentally measured sputtering rate of ZnO is 2.0 times higher than MgO when measured at the same conditions (supporting information), which is excellent agreement considering there are no adjustable parameters in Eqs.(8) and (9). Using the depth profiles in Fig.1, which were all measured at the same ion bombardment conditions, the sputtering rate of ZnS was measured to be 1.9 times higher than ZnO. Using Eqs.(8) and (9) it is predicted that the sputtering rate of ZnS would be 2.1 times higher than ZnO, again excellent agreement considering there are no adjustable parameters in the model. Thus we conclude that the model provides a fair thermodynamic description of the sputtering process for these ionic materials, and so next the model was used to measure the unknown CZTS. For details see the supporting information.

The sputtering rate of CZTS ($Cu_{1.9}Zn_{1.5}Sn_{0.8}S_4$) was measured to be 0.061 nm/s, while the sputtering rates of ZnS and ZnO were measured to be 0.065 nm/s and 0.035 nm/s respectively at the same conditions (Table 1). By rearranging Eq.(8) and using the measured sputtering rate ratio, the surface binding energy of CZTS was calculated to be 4.0 eV/atom by comparing to ZnO; and 3.6 eV/atom by comparing to ZnS. Averaging these values gives 3.8 eV/atom. Rearranging Eq.(9), using tabulated thermodynamic data (see the supporting information), and $U_{0,CZTS}$ = 3.8±0.4 eV/atom, the enthalpy of formation for CZTS is –1.2±0.13 eV/atom, –9.6±1.0 eV/molecule or –930±98 kJ/mol of $Cu_{1.9}Zn_{1.5}Sn_{0.8}S_4$ molecules.

Table 1. Summary of parameters used to calculate the enthalpy of formation for CZTS.

	$Cu_{1.9}Zn_{1.5}Sn_{0.8}S_4$	ZnO	ZnS	Units
SR	0.061	0.035	0.065	nm/s
ρ	4.6	5.6	4.1	g/cm^3
d	92	20	22	nm
M_t	53.91	40.69	48.72	a.m.u.
n	5.1×10^{22}	8.3×10^{22}	5.1×10^{22}	1/cm^3
α	0.29	0.26	0.27	–
γ	0.98	1.0	0.99	–
U_0	3.8	4.2	3.1	eV/atom
E_{coh}	31.2	8.4	6.2	eV/molecule
ΔH_f^0	–1.2±0.13	–1.80	–1.07	eV/atom
ΔH_f^0	–930±98	–347	–206	kJ/mol

A conclusion that can be drawn from the measured enthalpy of formation for multinary CZTS is that the reaction of the binary metal sulfides to form the multinary compound is exothermic. The reaction of the binary metal sulfides to form CZTS is reversible,[10] and can be written as:

$$Cu_2S + ZnS + SnS_2 \leftrightarrow Cu_2ZnSnS_4. \quad (R1)$$

The sum of the enthalpies of formation for the binary compounds is –437 kJ/mol (Table S4), which means the enthalpy change for reaction R1 is approximately –490 kJ/mol. This contrasts with the enthalpies of formation that have been reported using DFT approaches. Maeda et al.[3] and Walsh et al.[4] reported enthalpies of formation of –337 kJ/mol and –406 kJ/mol respectively, both of which predict that reaction R1 is endothermic with an enthalpy change of +100 kJ/mol and +31 kJ/mol respectively. Differential scanning calorimetric (DSC) measurements should be able to clearly determine whether reaction R1 is exothermic or endothermic, but such measurements are outside the scope of this communication.

Taking the analysis a step further, the Gibb's free energy of reaction can be calculated using our experimental enthalpy and those predicted by DFT. The free energy of reaction for R1 can be written in terms of the energies of formation:

$$\Delta G_r = \Delta G_{f,CZTS} - \Delta G_{f,binaries}. \quad (11)$$

The free energies of formation for the binary metal sulfides as a function of temperature are known, and the expressions can be found in the supporting information

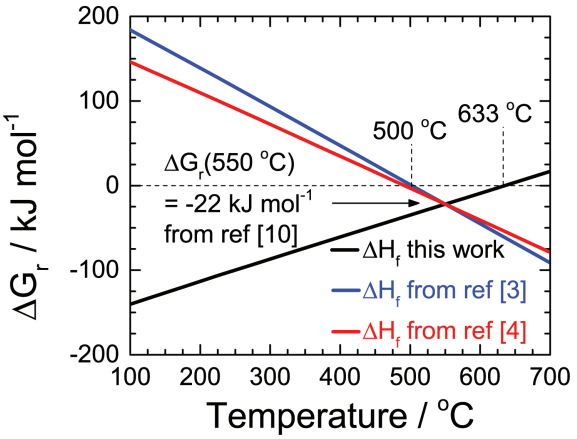

FIG. 2: ΔG_r **of reaction R1 using different values of the enthalpy of formation from Eq.(11). The** $\Delta S^0_{f,CZTS}$ **vales were –0.59, 0.13 and 0.046 kJ/(mol·K) using the enthalpies of this work, Ref[3] and Ref[4] respectively.**

(Eq.(S10)). The free energy of formation for CZTS as a function of temperature can be estimated by:

$$\Delta G_{f,CZTS} \approx \Delta H^0_{f,CZTS} - T \cdot \Delta S^0_{f,CZTS}. \quad (12)$$

The variables in Eqs.(11) and (12) are known except for $S^0_{f,CZTS}$ and ΔG_r. Scragg et al. reported a free energy of reaction for R1 ΔG_r(823 K)=–22±6 kJ/mol.[10] Thus we can solve Eqs.(11) and (12) for $S^0_{f,CZTS}$ using ΔG_r(823 K), and then plot the free energy of reaction for R1 as a function of temperature (Fig.2).

The enthalpy of formation measured in this work predicts a different trend in the free energy of reaction when compared to those predicted by DFT. An enthalpy of formation of –930 kJ/mol predicts that the CZTS formation reaction from the binary metal sulfides is favorable at low temperature, but becomes unfavorable at approximately 633 °C. Considering the margins of error, the temperature at which we predict the reaction R1 to become unfavorable is similar to the temperature of ∼550 °C where CZTS has been observed to decompose.[10–12] The DFT enthalpies of formation predict something quite different, however, namely an endothermic reaction favorable at high temperature since it is driven by an increase in entropy. Taken with the free energy of formation reported by Scragg et al., the DFT numbers predict the free energy of reaction to become negative only at high temperature, with the line crossing the horizontal axis at approximately 500 °C (Fig.2). Experimentally, multinary CZTS nanocrystals have been synthesized at temperatures as low as 150–180 °C.[13] We have deposited a $Cu_2S/SnS_2/ZnS$ multialyer by ALD with an overall film thickness of approximately 30 nm.[14] After annealing for 60 minutes at 300 °C in argon, this 30 nm multilayer structure exhibited a Raman spectrum consistent with the multinary CZTS phase, while it did not before annealing.[14] Riha et al. have synthesized CZTS nanocrystals at 300 °C.[15] Summarizing, taken with the free energy of reaction reported by Scragg et al.,[10] the consequences of the enthalpy value we have measured are 1) that the binaries should react to form the multinary phase at low temperature (if kinetic limitations are removed) and 2) that the multinary phase is unstable at 630 °C (or even before because the reaction is reversible); both of which have been experimentally observed.

There is a consequence for CZTS film processing. A number of authors have reported on tin and sulfur loss from CZTS at elevated temperatures that results from the SnS_2 (reaction R1) decomposing into SnS and S_2, both of which are volatile.[10] The SnS_2 decomposition can be suppressed by including sulfur or tin monosulfide in the annealing environment at sufficiently high vapor pressure.[10,12] Our hypothesis is that a significant quantity of binary phases should be present at high temperature, even if SnS_2 decomposition is suppressed. However, since reaction R1 is reversible, and the multinary phase is favored at low temperature (Fig.2), these binary phases should react back into the multinary phase as the material cools, and only the multinary phase should be observable at low temperature for sufficiently slow cooling rates, provided SnS_2 decomposition has been suppressed. However, if the material is rapidly quenched, we may expect that there will be significant impurity content, since the binary compounds would have insufficient time to react back into the multinary phase. In short, for rapid quenching, binary impurities would be kinetically frozen into the film.

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